

UTC UNISONIC TECHNOLOGIES CO., LTD

2N7002LL

Preliminary

60V, 115mA N-CHANNEL **POWER MOSFET**

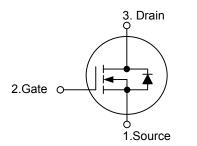
DESCRIPTION

The UTC 2N7002LL uses advanced technology to provide excellent R_{DS(ON)}, low gate charge and operation with low gate voltages. This device is suitable for use as a load switch or in PWM applications.

FEATURES

- * $R_{DS(ON)}$ < 7.5 Ω @ V_{GS} =10V, I_D =115mA
- * Low Reverse Transfer Capacitance (C_{RSS} = typical 5 pF)
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL

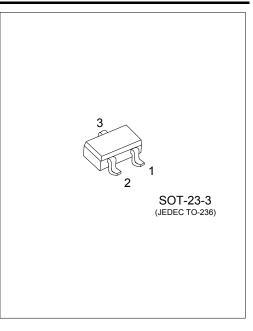


ORDERING INFORMATION

Ordering Number	Deekege	Pin Assignment			Packing	
Ordering Number	Package	1	2	3	Facking	
2N7002LLG-AE2-R	SOT-23-3	S	G	D	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source						
2N7002LLG-AE2-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel(2) AE2: SOT-23-3(3) G: Halogen Free and Lead Free					

MARKING





■ ABSOLUTE MAXIMUM RATINGS (T_A =25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	60	V	
Drain-Gate Voltage (R _G =1.0MΩ)		V _{DGR}	60	V	
Gate-Source Voltage	Continuous	V _{GSS}	±20	V	
	Non-repetitive (t _P \leq 50µs)	V _{GSM}	±40	V	
Drain Current	Continuous(T _C =25°C)		115		
	Pulse(Note 2)	I _D	460	mA	
Power Dissipation ($T_A = 25^{\circ}C$)			225	mW	
Derate above 25°C		PD	1.8	mW /°C	
Junction Temperature		ΤJ	+150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

 Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Pulse width ≤ 300µs, Duty cycle ≤ 2%

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	556	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, Ι _D =10μΑ	60			V		
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V (T _J =25°C)			1.0	μA		
Gate-Source Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V			±100	nA		
ON CHARACTERISTICS(Note)								
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250 μA	1.0		2.5	V		
Drain-Source On-State Voltage	V _{DS(ON)}	V _{GS} =10V, I _D =115mA			3.75	V		
		V _{GS} =5V, I _D =50mA			0.375	5 V		
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =115mA(T _C =25°C)			7.5			
		V_{GS} =5V, I_{D} =50mA(T_{C} =25°C)			7.5	Ω		
DYNAMIC PARAMETERS								
Input Capacitance	CISS				50	pF		
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V, f=1.0MHz			25	pF		
Reverse Transfer Capacitance	C _{RSS}				5.0	pF		
SWITCHING PARAMETERS								
Turn-ON Delay Time	t _{D(ON)}	V _{DD} =25V, I _D =115mA,			20	ns		
Turn-OFF Delay Time	t _{D(OFF)}	V_{GEN} =10V, R_G =25 Ω , R_L =50 Ω			40	ns		
SOURCE- DRAIN DIODE RATINGS AND (CHARACTER	RISTICS						
Diode Forward Voltage	V_{SD}	I _S =115mA, V _{GS} =0V			1.5	V		
Maximum Body-Diode Continuous Current	ls				115	mA		
Source Current Pulsed	I _{SM}				115	mA		
Note: Dules Test: Dules Width < 200us, Dut								

Note: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2.0%.



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